



**CHENMKO ENTERPRISE CO.,LTD**

*Lead free devices*

**SURFACE MOUNT  
NPN Digital Silicon Transistor**

**VOLTAGE 50 Volts CURRENT 30 mAmpere**

**CHDTC144VUPT**

**APPLICATION**

- \* Switching circuit, Inverter, Interface circuit, Driver circuit.

**FEATURE**

- \* Small surface mounting type. (SC-70/SOT323)
- \* High current gain.
- \* Suitable for high packing density.
- \* Low collector-emitter saturation.
- \* High saturation current capability.
- \* Internal isolated NPN transistors in one package.
- \* Built in bias resistor( $R_1=47\text{k}\Omega$ , Typ. )

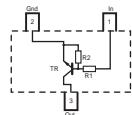
**CONSTRUCTION**

- \* One NPN transistors and bias of thin-film resistors in one package.

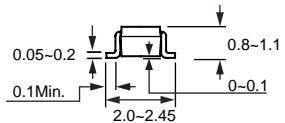
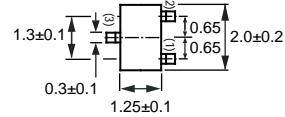
**MARKING**

VUA

**CIRCUIT**



**SC-70/SOT-323**



Dimensions in millimeters

**SC-70/SOT-323**

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CC</sub>	Supply voltage		–	50	V
V <sub>IN</sub>	Input voltage		-15	+40	V
I <sub>O</sub>	DC Output current		–	30	mA
I <sub>C(MAX.)</sub>			–	100	
P <sub>TOT</sub>	Total power dissipation	T <sub>amb</sub> ≤ 25 °C, Note 1	–	200	mW
T <sub>TSG</sub>	Storage temperature		-55	+150	°C
T <sub>J</sub>	Junction temperature		–	150	°C
R <sub>θJ-S</sub>	Thermal resistance	junction - soldering point	–	140	°C/W

**Note**

- Transistor mounted on an FR4 printed-circuit board.

## RATING CHARACTERISTIC ( CHDTC144VUPT )

### CHARACTERISTICS

$T_{amb} = 25^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{I(off)}$	Input off voltage	$I_o=100\mu\text{A}; V_{cc}=5.0\text{V}$	1.0	—	—	V
$V_{I(on)}$	Input on voltage	$I_o=2\text{mA}; V_o=0.3\text{V}$	—	—	6.0	V
$V_{O(on)}$	Output voltage	$I_o=10\text{mA}; I_i=0.5\text{mA}$	—	0.1	0.3	V
$I_i$	Input current	$V_i=5\text{V}$	—	—	0.16	mA
$I_{C(off)}$	Output current	$V_i=0\text{V}; V_{cc}=50\text{V}$	—	—	0.5	$\mu\text{A}$
$h_{FE}$	DC current gain	$I_o=5\text{mA}; V_o=5.0\text{V}$	33	—	—	
$R_1$	Input resistor		32.9	47	61.1	$\text{k}\Omega$
$R_2/R_1$	Resistor ratio		0.17	0.21	0.26	
$f_T$	Transition frequency	$I_E=-5\text{mA}, V_{CE}=10.0\text{V}$ $f=100\text{MHz}$	—	250	—	MHz

#### Note

1. Pulse test:  $t_p \leq 300\mu\text{s}$ ;  $\delta \leq 0.02$ .